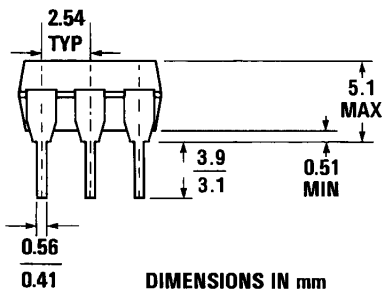
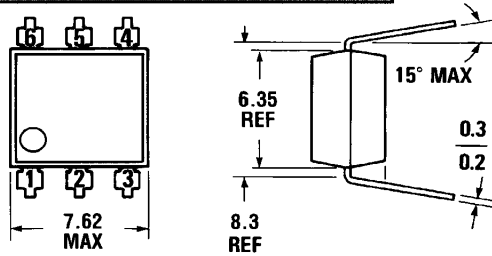
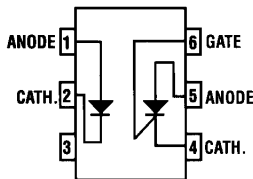


PACKAGE DIMENSIONS



ST1603



ST1602

Equivalent Circuit

DESCRIPTION

The 4N39 and 4N40 have a gallium-arsenide infrared emitting diode optically coupled with a light activated silicon controlled rectifier in a dual in-line package.

FEATURES & APPLICATIONS

- High efficiency, low degradation, liquid epitaxial LED
- 10 A, T²L compatible, solid state relay
- 25 W logic indicator lamp driver
- 400 V symmetrical transistor coupler
- Underwriters Laboratory (UL) recognized — File #E90700

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

- *Storage temperature -55°C to 150°C
- *Operating temperature -55°C to 100°C
- *Lead solder temperature 260°C for 10 sec
- *Total power dissipation (-55°C to 50°C) .. 450 mW
Derate linearly (above 50°C) 9.0 mW/°C

INPUT DIODE

- *Power dissipation (-55°C to 50°C) 100 mW
Derate linearly (above 50°C) 2 mW/°C
- *Continuous forward current (-55°C to 50°C) 60 mA
- *Peak forward current (-55°C to 50°C) 1 A
- *Reverse voltage (-55°C to 50°C) 6 V

DETECTOR

- *Power dissipation (-55°C to 50°C) 400 mW
Derate linearly (above 50°C) 8 mW/°C
- *Off-state and reverse voltage 4N39 200 V
*(-55°C to +100°C) 4N40 400 V
- *Peak reverse gate voltage(-55°C to 50°C) 6 V
- *Direct on-state current (-55°C to 50°C) 300 mA
- *Surge on-state current (-55°C to 50°C) (100µS) 10 A
- *Peak gate current (-55°C to 50°C) 10 mA

*Indicates JEDEC Registered Data



PHOTO SCR OPTOCOUPLERS

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ$ Unless Otherwise Specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
*Forward voltage	V_F		1.1	1.5	V	$I_F = 10$ mA
*Reverse leakage current	I_R			10	μ A	$V_R = 3$ V
Capacitance	C_J		50		pF	$V = 0$ V, $f = 1$ MHz
OUTPUT DETECTOR						
*Peak off-state voltage	(4N39) V_{DM}	200			V	$R_{GK} = 10$ k Ω , $T_A = 100^\circ$ C
	(4N40) V_{DM}	400			V	$R_{GK} = 10$ k Ω , $T_A = 100^\circ$ C
*Peak reverse voltage	(4N39) V_{RM}	200			V	$T_A = 100^\circ$ C
	(4N40) V_{RM}	400			V	$T_A = 100^\circ$ C
*On-state voltage	V_T			1.3	V	$I_T = 300$ mA
*Off-state current	(4N39) I_{DM}			50	μ A	$V_{DM} = 200$ V, $T_A = 100^\circ$ C, $I_F = 0$, $R_{GK} = 10$ K Ω
	(4N40) I_{DM}			150	μ A	$V_{DM} = 400$ V, $T_A = 100^\circ$ C, $I_F = 0$, $R_{GK} = 10$ K Ω
*Reverse current	(4N39) I_R			50	μ A	$V_R = 200$ V, $T_A = 100^\circ$ C, $I_F = 0$
	(4N40) I_R			150	μ A	$V_R = 400$ V, $T_A = 100^\circ$ C, $I_F = 0$
*Holding current	I_R			1.0	mA	$V_{F_A} = 50$ V, $R_{GK} = 27$ k Ω

TRANSFER CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
*Input current to trigger	(4N39, 4N40) I_{FT}			30	mA	$V_{AK} = 50$ V, $R_{GK} = 10$ k Ω
	(4N39, 4N40) I_{FT}			14	mA	$V_{AK} = 100$ V, $R_{GK} = 27$ k Ω
*Turn-on time	t_{on}			50	μ s	$V_{AK} = 50$ V, $I_F = 30$ mA, $R_{GK} = 10$ k Ω , $R_L = 200$ Ω
Package capacitance (input to output)				2	pF	Input to output voltage=0 $f = 1$ MHz
Coupled dv/dt, input to output (figure 13)		500			V/ μ s	

ISOLATION CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Surge isolation voltage	V_{ISO}	7500			V	1 Minute
Isolation voltage	V_{ISO}	5300			V	1 Minute
*Isolation resistance	R_{ISO}	10^{11}			ohms	$V_{IO} = 500$ VDC

*Indicates JEDEC Registered Data

TYPICAL CHARACTERISTICS OF OUTPUT (SCR)

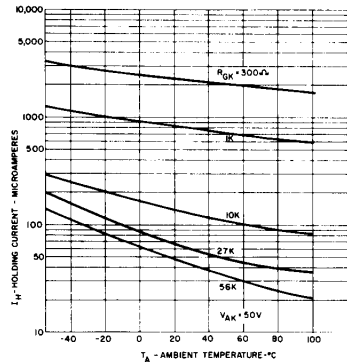


Figure 7. Holding Current vs. Temperature

ST2111

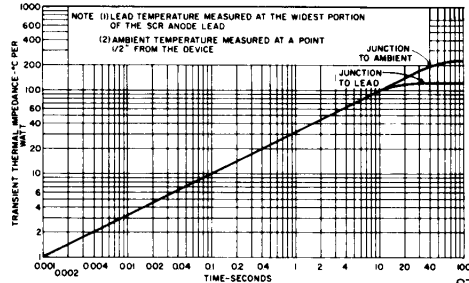


Figure 8. Maximum Transient Thermal Impedance

ST2112

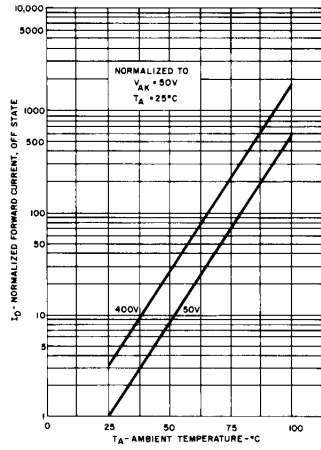


Figure 9. Off-State Forward Current vs. Temperature

ST2113

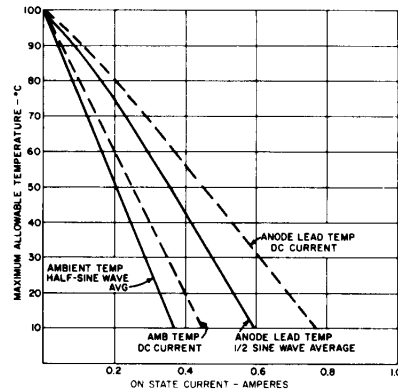


Figure 10. On-State Current vs. Maximum Allowable Temperature

ST2114

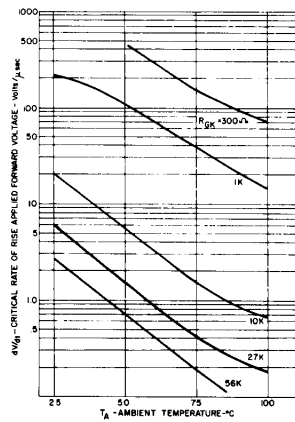


Figure 11. dv/dt vs. Temperature

ST2115

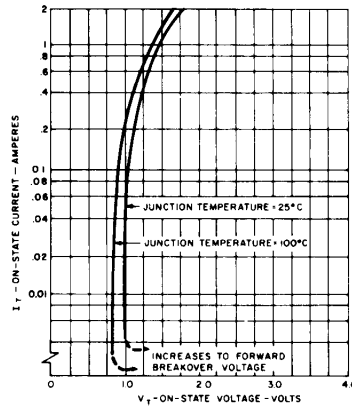


Figure 12. On-State Characteristics

ST2116

TYPICAL ELECTRO-OPTICAL CHARACTERISTICS

($T_A = 0^\circ\text{C}$ to 70°C Unless Otherwise Specified)

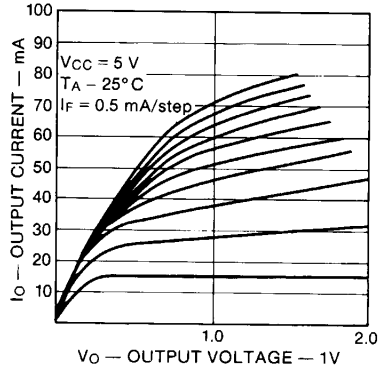


Fig. 1. DC Transfer Characteristics

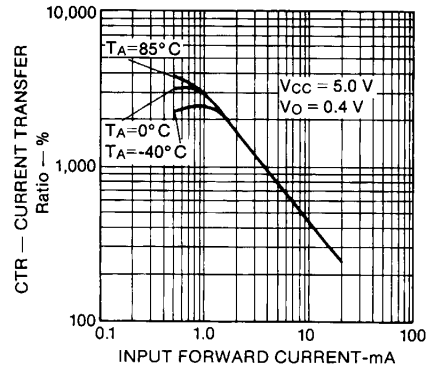


Fig. 2. Current Transfer Ratio vs. Input Forward Current

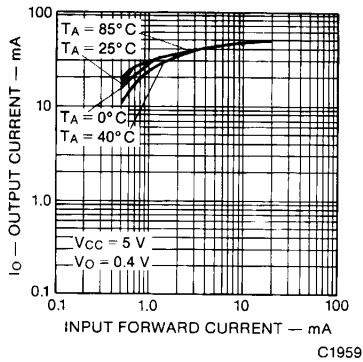


Fig. 3. Output Current vs. Input Forward Current

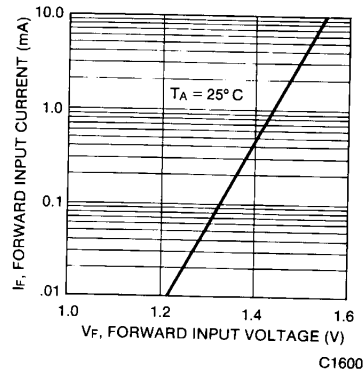


Fig. 4. Forward Input Current vs. Forward Input Voltage

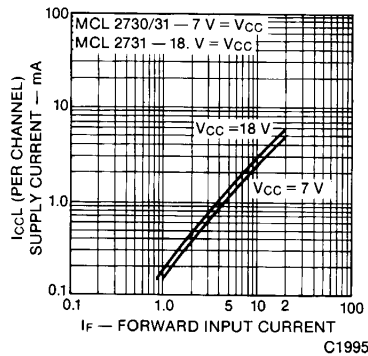
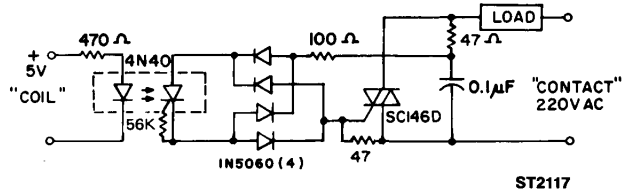


Fig. 5. Supply Current Per Channel vs. Input Forward Current

TYPICAL APPLICATIONS

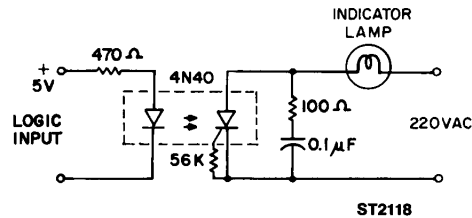
10A, T²L COMPATIBLE, SOLID STATE RELAY

Use of the 4N40 for high sensitivity, 5300V isolation capability, provides this highly reliable solid state relay design. This design is compatible with 74, 74S and 74H series T²L logic systems inputs and 220V AC loads up to 10A.



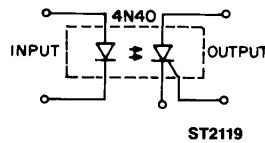
25W, LOGIC INDICATOR LAMP DRIVER

The high surge capability and non-reactive input characteristics of the 4N40 allow it to directly couple, without buffers, T²L and DTL logic to indicator alarm devices, without danger of introducing noise and logic glitches.



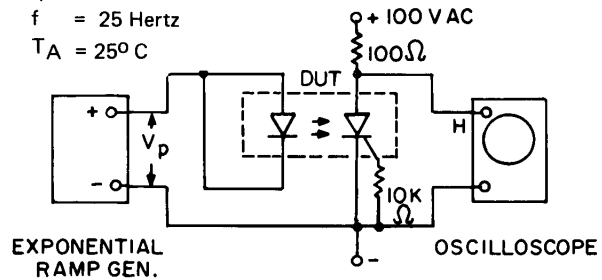
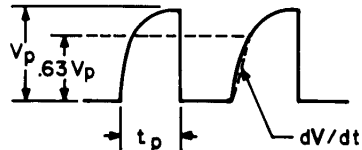
400V SYMMETRICAL TRANSISTOR COUPLER

Use of the high voltage PNP portion of the 4N40 provides a 400V transistor capable of conducting positive and negative signals with current transfer ratios of over 1%. This function is useful in remote instrumentation, high voltage power supplies and test equipment. Care should be taken not to exceed the 400 mW power dissipation rating when used at high voltages.



**FIGURE 13
COUPLED dv/dt - TEST CIRCUIT**

$V_p = 800$ Volts
 $t_p = .010$ Seconds
 $f = 25$ Hertz
 $T_A = 25^\circ$ C



ST2120